



INFORMATION DISCLOSURE CITATION		ATTY. DOCKET NO.			SERIAL NO.
		1035-650			10/589,390
		APPLICANT			
		IMAI ET AL.			
(Use several sheets if necessary)		FILING DATE	GROUP		
		August 15, 2006	2812		
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
/PD/	2003/0102793	6-2003	Komoda et al.		
/PD/	2005/0215070	9-2005	Kobayashi		
/PD/	6,221,788	4-2001	Kobayashi et al.		
FOREIGN PATENT DOCUMENTS					
DOCUMENT			COUNTRY	TRANSLATION	
DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES NO
/PD/	3-6826 A	1-1991	JP		Partial
▼	52-78374	1-1977	JP		Partial
	2002-57154 A	2-2002	JP		Partial
/PD/	2002-64093 A	2-2002	JP		Partial
OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)					
/PD/	Sakamoto et al, "Formation of Anodic Reaction Film on n-type Si", Applied Physics, vol. 44, Issue No. 5, 1975, pp.497-506				
↓	Tokuyama, "Comprehensive Treatise on Electronics Technology", Vol. 3, MOS Device, Kogyochosakai, 1976, pp.124-126				
↓	Asusha et al, "Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density Formed by Chemical Oxidation of Si", Applied Physics Letters, Vol. 81, No. 18, 28 October 2002, pp. 3410-3412				
↓	Kobayashi et al, "Nitric Acid Oxidation of Si to Form Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density", Journal of Applied Physics, Vol. 94, No. 11, American Institute of Physics, 2003, pp. 7328-7335				
/PD/	Asuha et al, "Low Temperature Formation of Sio ₂ /Si Structure by Chemical Method and Spectroscopic Observation", Meeting Abstracts of the Physical Society of Japan, Vol. 58, Issue 2, Part 4, Meeting Abstracts, 2003, pp. 771-				

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)